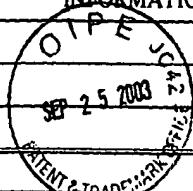


U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.	Serial No.			
				M-15230 US	10/632,154			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Yi Ding				
APR 20 2004				Filing Date	Group			
				July 30, 2003	Unassigned 2823			
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							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

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KN	AT	United States Patent Application No. 10/440,005, entitled "Fabrication of Dielectric On A Gate Surface To Insulate The Gate From Another Element Of An Integrated Circuit," Filed on May 16, 2003; Attorney Docket No.: M-15203 US.	
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(Use several sheets if necessary)		Yi Ding	
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		July 30, 2003	Unassigned 2823
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	BF		
	BG		
	BH		
Examiner <i>Yi Ding</i>	Date Considered	07/23/04	
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		Filing Date 07/30/03	Group
		Filed Herewith	Unassigned 2823

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		M-15230 US	Unassigned 16/632154
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		Yi Ding	
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		Filed Herewith	Unassigned 2823

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Y	BH	
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